

ABSTRACT

A semiconductor device includes a gate structure including insulating layers and conductive layers alternately stacked, channel structures extending through the gate structure and arranged in a first direction and a second direction crossing the first direction, a slit structure extending in the first direction and including a body portion and protrusions protruding from the body portion in the second direction, and dummy structures arranged in the first direction between the channel structures and the slit structure and respectively contacting the protrusions.

FIG. 1A